

The background of the slide is a photograph of the Aurora Borealis (Northern Lights) in a dark night sky. The aurora appears as vibrant green and blue curtains of light. Below the sky, the dark silhouettes of evergreen trees are visible against the horizon.

# Interaction of heavy charged particles and ions with matter

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## Introduction

## Particle/ion-atom interactions

- basic processes on energy loss
- stopping power, range

## Implementation in Nucleonica™

## Examples





# Origin and use of particles

## Particles

$e^-$

$n$

$p^+$

$d^+$

$\alpha$

heavy ions

## Origin

Cosmic rays

Radioactivity

- natural

- artificial

Accelerators

## Use

medicine

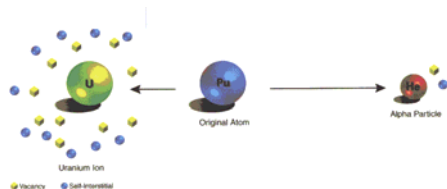
industry

research

radioprotection



# Range of different particles



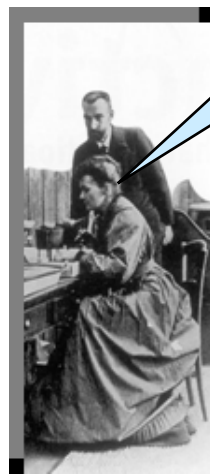
	Energy, keV	Range, $\mu\text{m}$	dE/dx, Nucl./Elec.	Defects formed
Light FPs	95000	9	0.03/0.97	40000
Heavy FPs	67000	7	0.06/0.94	60000
$\alpha$ -particles	5000	12	0.01/0.99	200
Recoil nucleus	95	0.02	0.90/0.10	1500
Cosmic rays ( $p^+$ )	$10^{17}$ $10^6$ (typical)	Light years !		



“Les rayons alpha sont des projectiles matériels susceptibles de perdre de leur vitesse en traversant la matière” (1900)



H. Becquerel



P. Curie



E. Rutherford

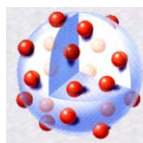


N. Bohr

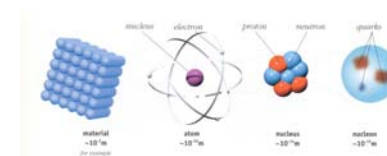
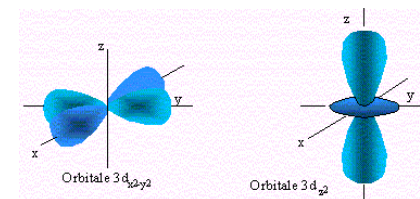
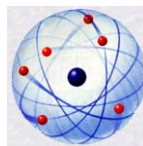
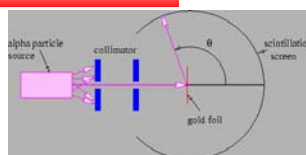
E. Fermi



E. Schrödinger



M. Curie-Slodowska



1896

1911

today....





Slowing down of a particle/ion in a target

- history of the particle  
energy loss of a particle, range, interactions
- history of the target atoms  
displacements, recombinations, ionization,  
excitation, radiation damage build-up

## Areas of interest

Nuclear industry, nuclear medicine, space applications,  
semi-conductor, geology...





# Interaction of a charged particle with matter

## Inelastic collisions with an electron

main process of energy loss producing excitation and ionization

## Inelastic collisions with a nucleus

Bremsstrahlung and coulombic excitation

## Elastic collisions with a nucleus

Rutherford diffusion

## Elastic collisions with an electron



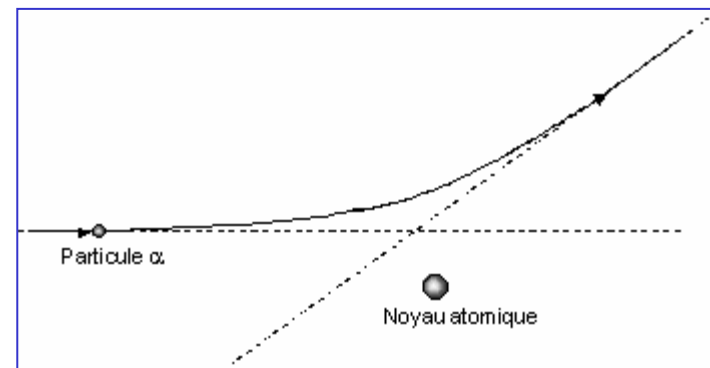


$$\frac{1}{2}M_1v_1^2 = \frac{1}{4\pi\epsilon_0} \frac{Z_1Z_2e^2}{D}$$

D was measured by Rutherford.

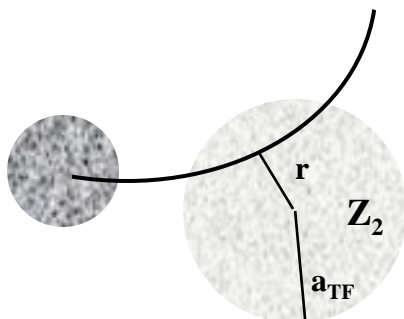
The minimum D value indicated the upper limit of the nuclei radius.

- Many interactions are needed to stop the particle (low probability of energy transfer).
- the probability to transfer energy is inverse to the mass of the target particle (mainly electrons will participate).
- Probability higher at low velocity (end of range).





....In fact..



Screening of  $e^-$  : Thomas-Fermi potential

$$V(r) = \Phi\left(\frac{r}{a_L}\right) \frac{Z_1 Z_2 e^2}{r}$$

with the screening length (Lindhard)

$$a_L = \frac{0.8853}{(Z_1^{2/3} Z_2^{2/3})^{1/2}} a_0$$

## Interatomic potential

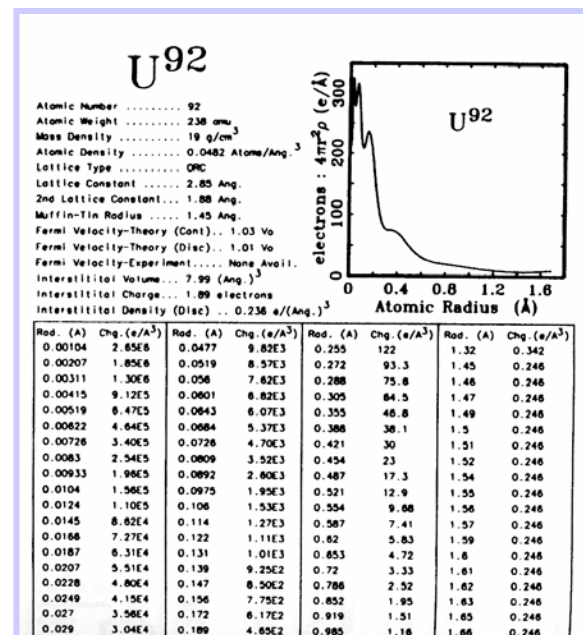
Other description of the screening function by Lenz, Jensen, Sommerfeld, Moliere

Inter-penetration of the electron clouds

Hartree-Fock-Slater calculations

However, good approximation by TF

## Charge distribution in single atom





- CSDA range: the continuous slowing down approximation range is obtained by integrating the reciprocal of the total stopping power with respect to the energy.
- The projected range is the value of the depth measured along the initial direction at which a charged particle/ion will be at rest.



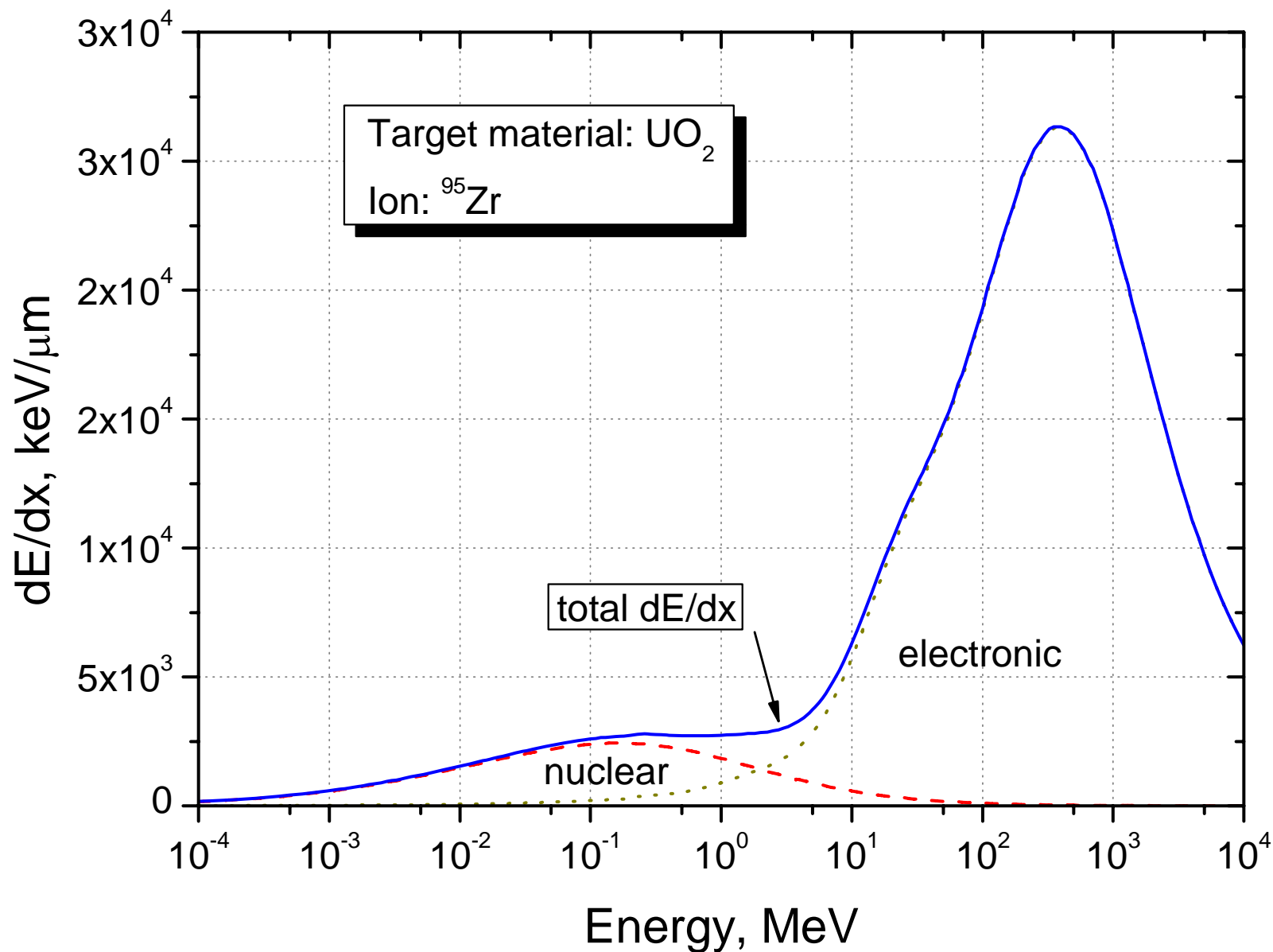


The Range program is a user friendly module for the calculations of the **stopping power and range** of charged particle in matter.

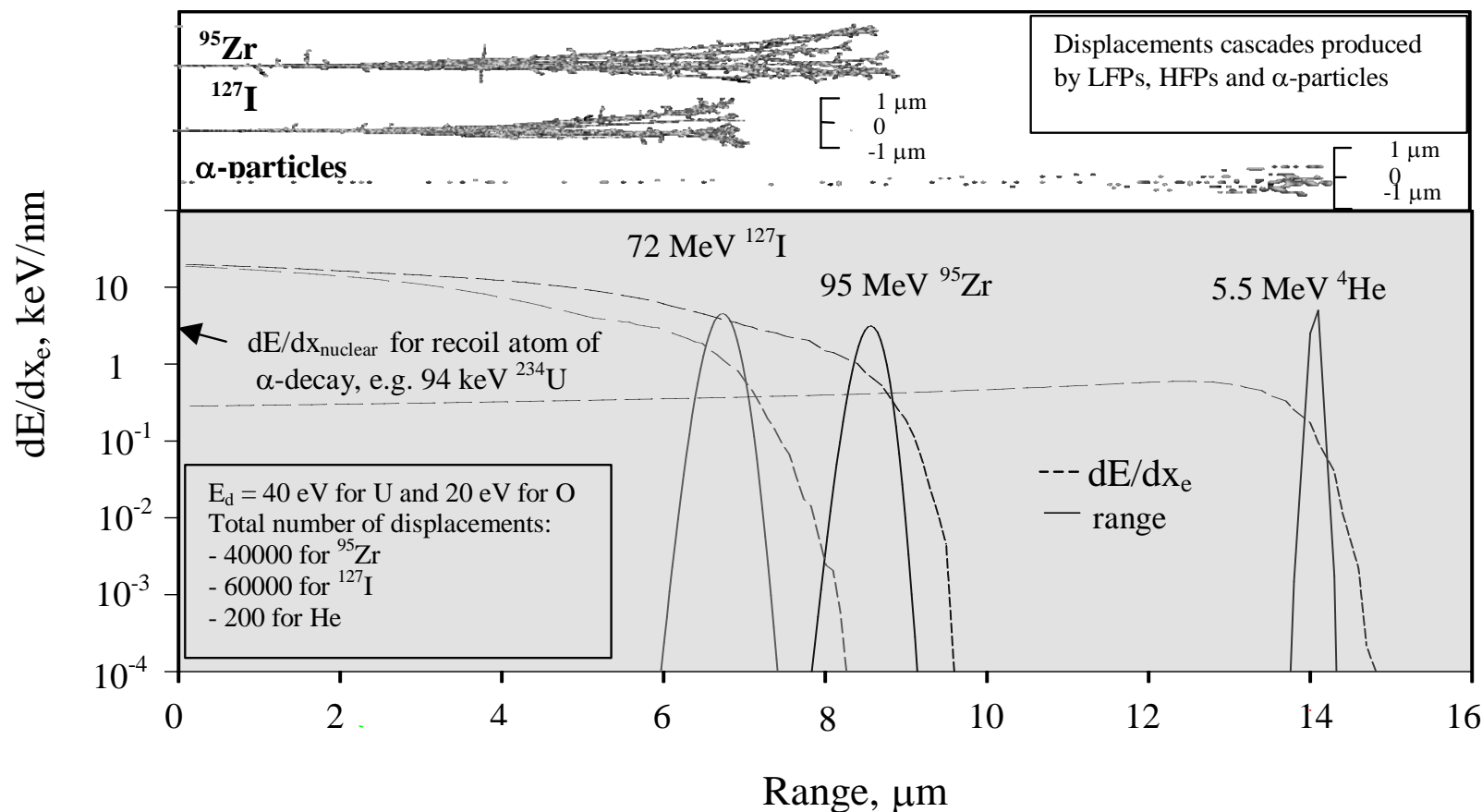
For ions, the SR\_module from SRIM is used to calculate stopping powers and ranges for ions (with energy up to 2 GeV/amu) up to uranium with an accuracy of about 3-4% to the measured values.

- J. P. Biersack and J. F. Ziegler, "The Calculation of Ion Ranges in Solids with Analytic Solutions", 157-176, in "Ion Implantation Techniques", H. Ryssel and H. Glawischnig, Springer Verlag, Berlin (1982).
- J. F. Ziegler, J. P. Biersack and U. Littmark, "The Stopping and Range of Ions in Matter", Pergamon Press, New York (1985).



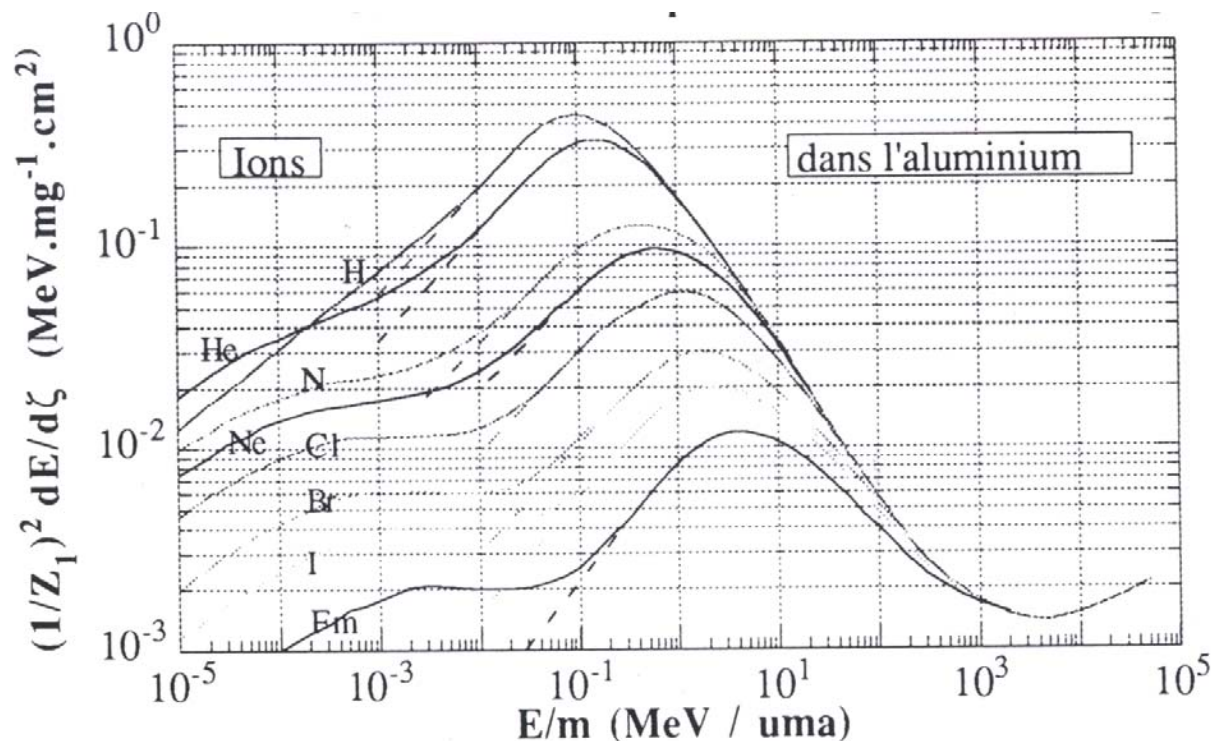


# Stopping power and ranges



# Stopping power of heavy ions

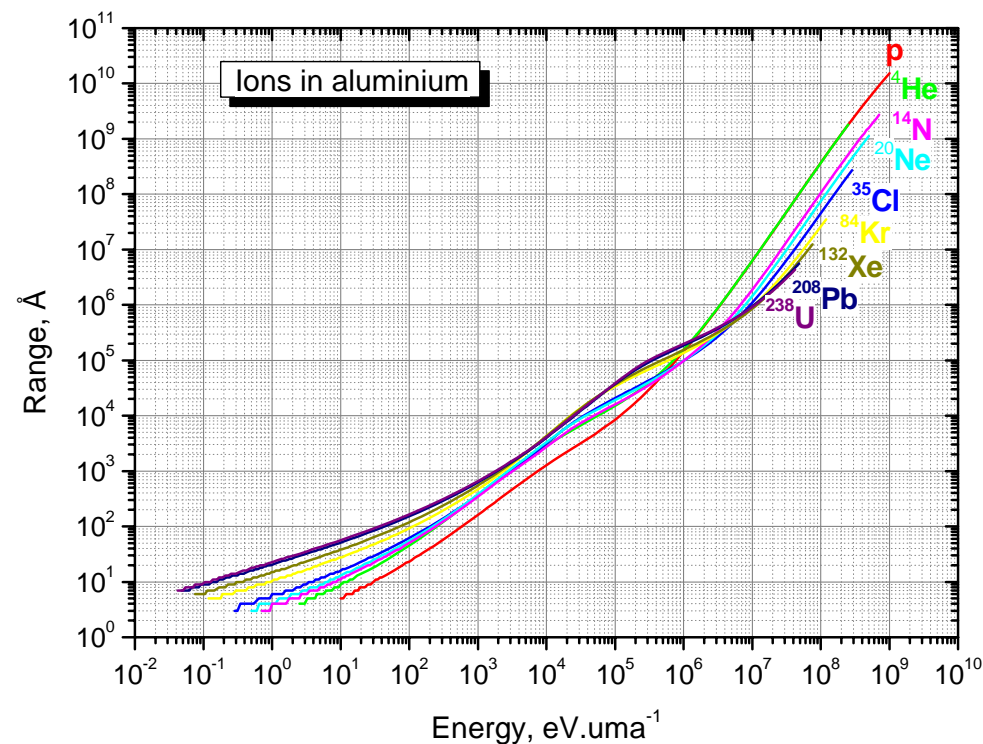
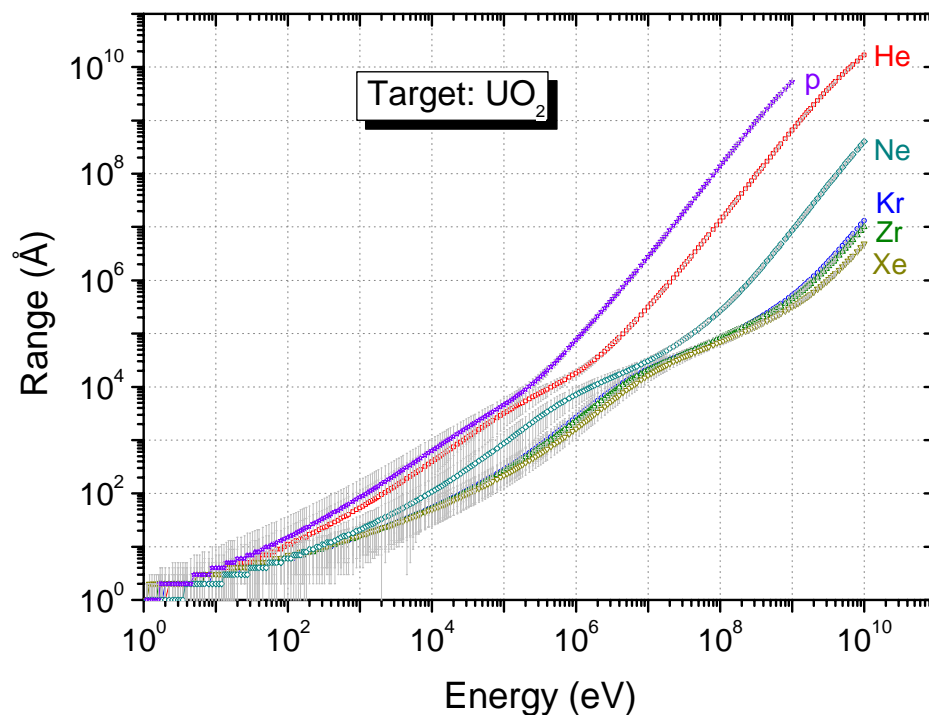
The stopping power for heavy ions can be assessed by the Bethe-Bloch approach but needs to be corrected by the effective charge (dependant on the velocity).



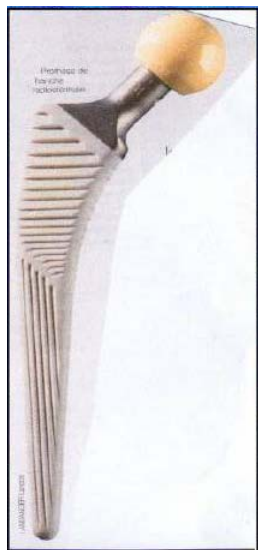
At high energy the curves of the heavy ions join the one of the proton.  
From one medium to another  $Z/A$  correction.



# Range of various particles/ions

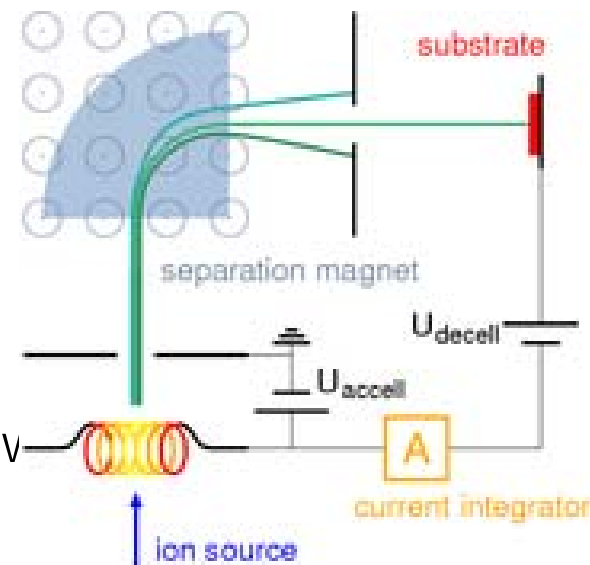






## Physical and chemical modifications

- Compression of the irradiated surface
- Amorphisation, formation of metallic glasses.
- Creation of supersaturated solid solutions.
- Precipitation of phases into small grains.
- Formation of a passive layer.
- Modification of the surface energy/chemical reactivity
- Enhanced oxide layer formation.



**Ion implantation** allows combination of many substrate and implanted species.

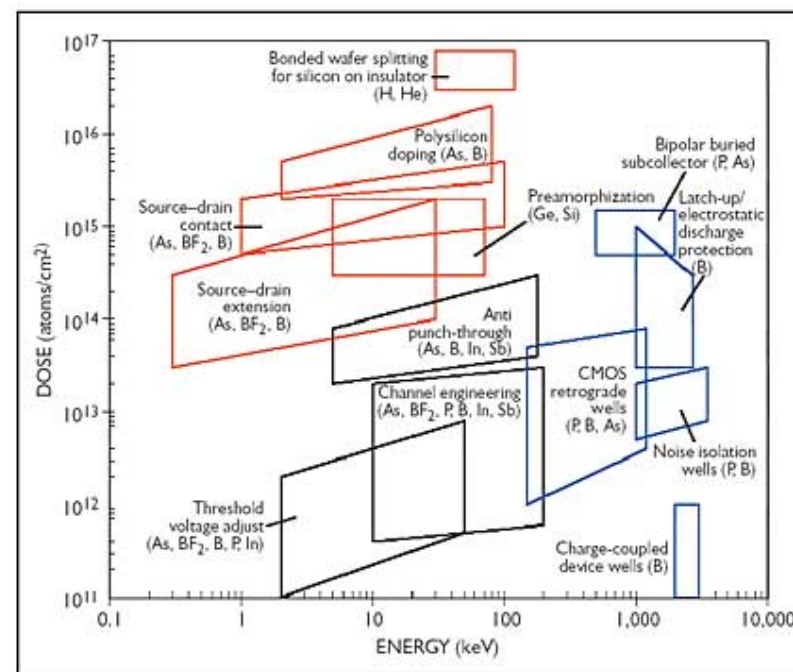
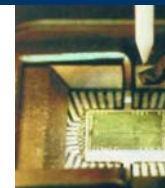
Materials	Applications	Implanted species	Improvement factor
Ti-6Al-4V, CoCrMo, UHMWPE	reduction of articular prostheses wear (e.g. hip)	N	x 8 to 100
Silicone	catheters thrombo-resistance	N, O, C, Ar	x 10
Silicone	antibacterial surfaces for catheters	Ag	100 % bacteria disappearance

# Ion implantation: applications

Properties	MECHANIC	CORROSION	PHYSICO-CHEMICAL PROPERTIES
Improvements	Wear Friction Fatigue	High T° oxidation Water corrosion Hydrogen adsorption Salt corrosion	Surface energy Adhesion Chemical activity Catalysis
Domain	Spatial Aeronautics Mechanics Tools Biomedical Instrumentation	Chemical Industry Aeronautics Engines, turbines Corrosive products Nuclear Wet and aqueous products Biomedical	Biocompatibility in general Hemo-compatibility Cyto-compatibility. Antithrombogenic action

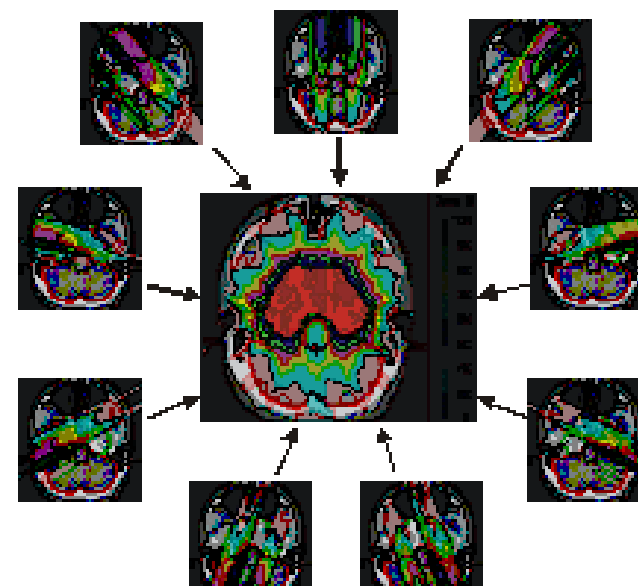
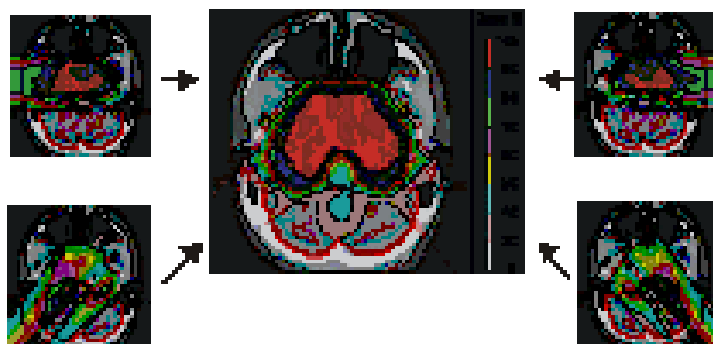
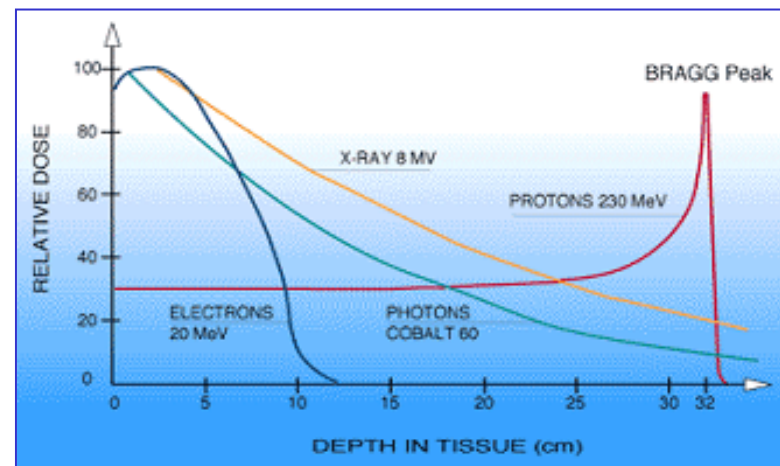
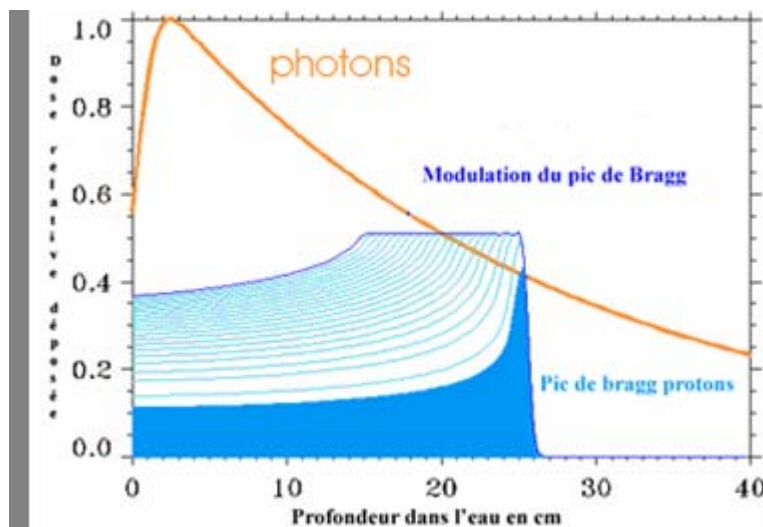
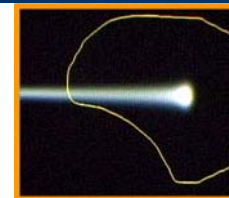


The majority of integrated circuits are fabricated from single crystal silicon wafers doped with Group III elements ( B, Al, Ga, In ,Tl), p-type, or with Group V elements ( N, P, As, Sb, Bi), n type. Transistors are formed by junctions between n-type and p-type silicon in the sequences n-p-n or p-n-p. Dopants are impurity elements added to the semiconductor crystal to form electrical junctions or boundaries between "n" and "p" regions in the crystal. The most common doping methods include diffusion and **ion implantation**.



# Protontherapy

- Protontherapy (used in treatment of tumors)  
200 MeV p+ can penetrate in 22 cm tissue

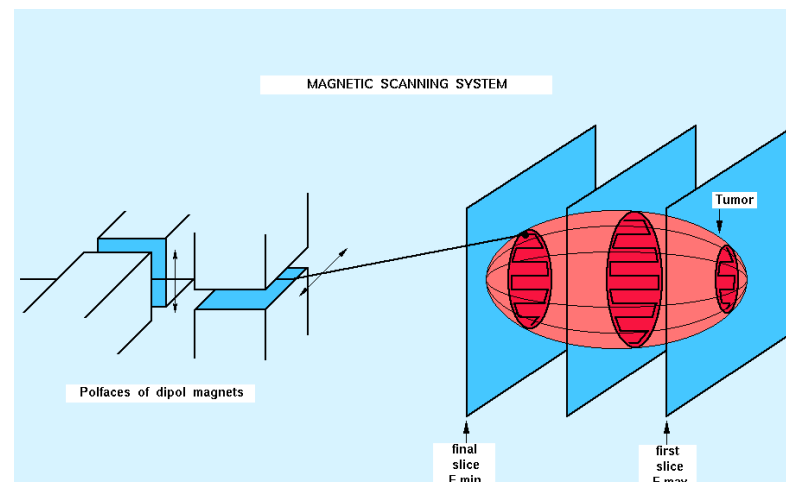
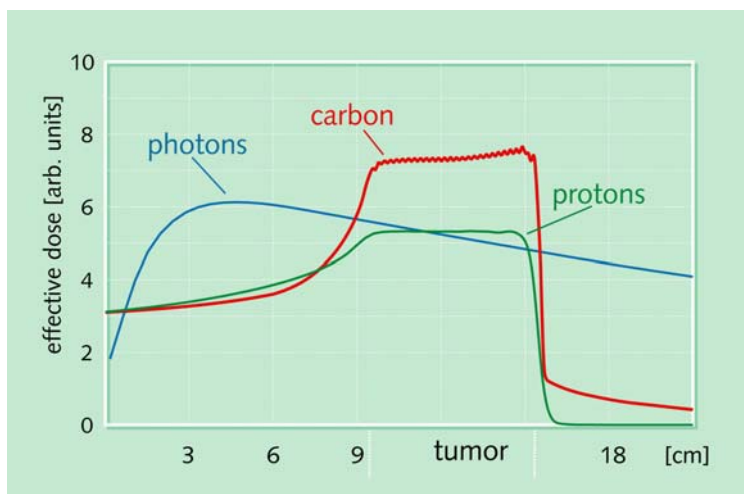


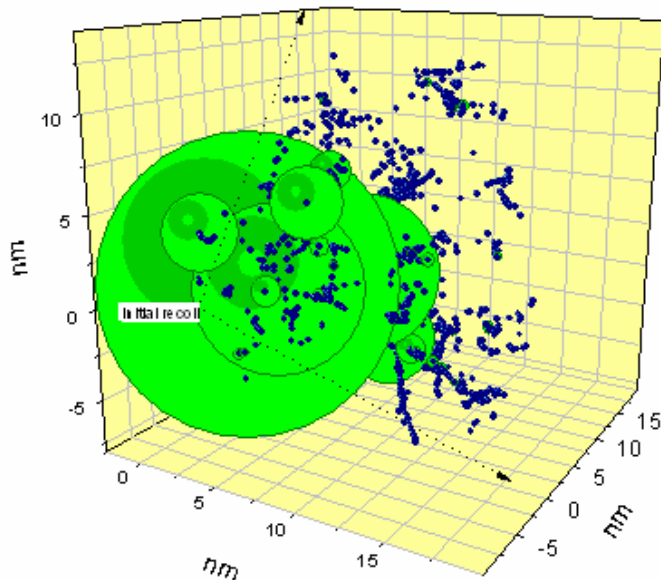


Tumour patients (head region) have been treated with accelerated carbon ions beams at GSI since the end of 1997.

- aim carbon ions directly at the tumour with great precision.
- high biological efficiency of carbon ions.

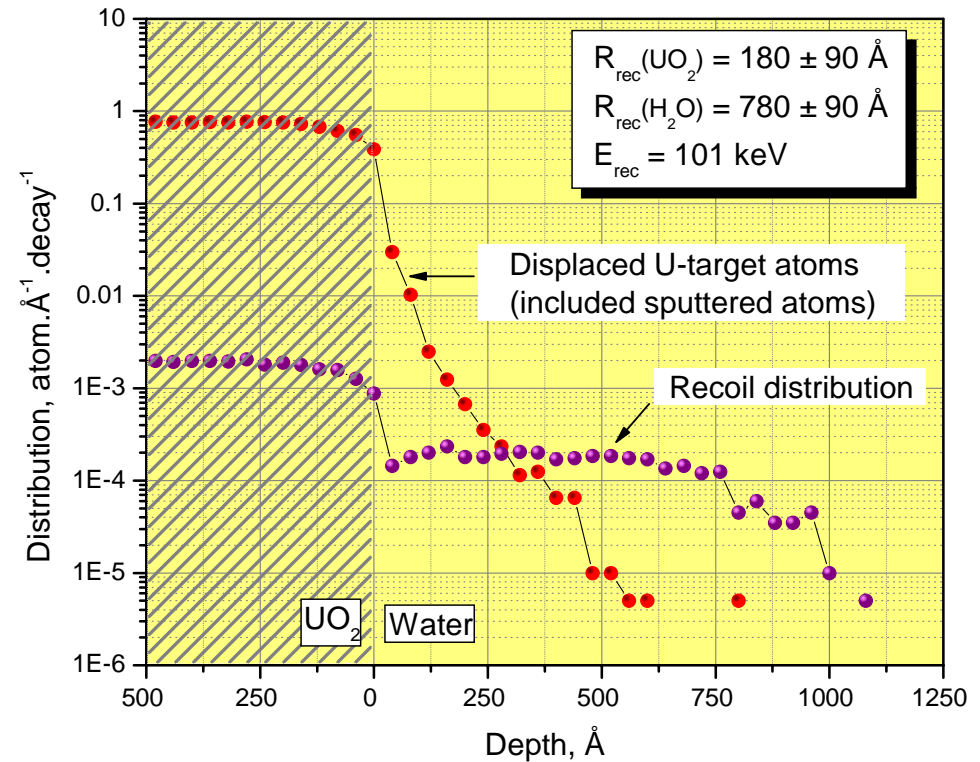
Based on the studies at GSI, a therapy centre in Heidelberg is being built where up to 1,000 patients per year could be treated.





Cascade from recoil

Distribution in water of the emitted recoil atoms from spent fuel surface



## Radiolysis effects

AURORA BOREALIS  
*Marc Wächter*

END...

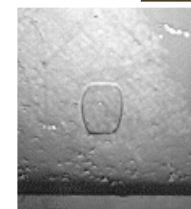
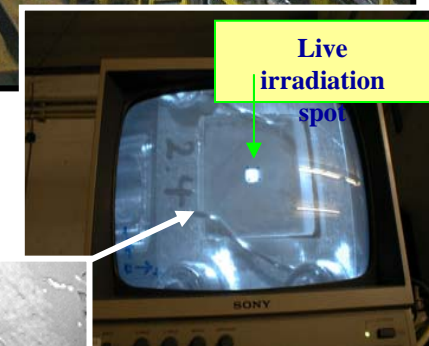
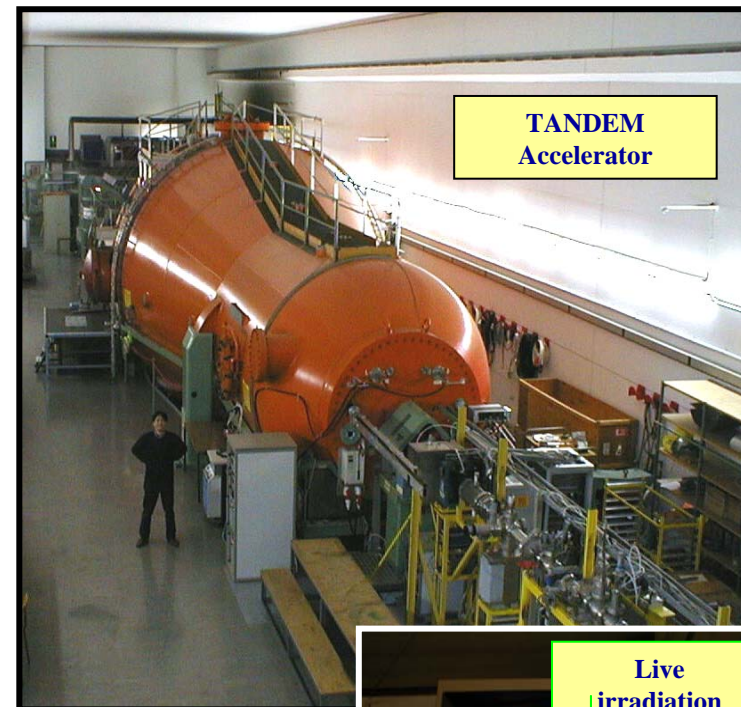




To simulate fission damage in a material candidate for transmutation of actinides, a single crystal sample ( $\text{Al}_2\text{O}_3$ ) will be implanted with:

70 MeV iodine (heavy fission product) and 100 MeV Zr (light fission product)

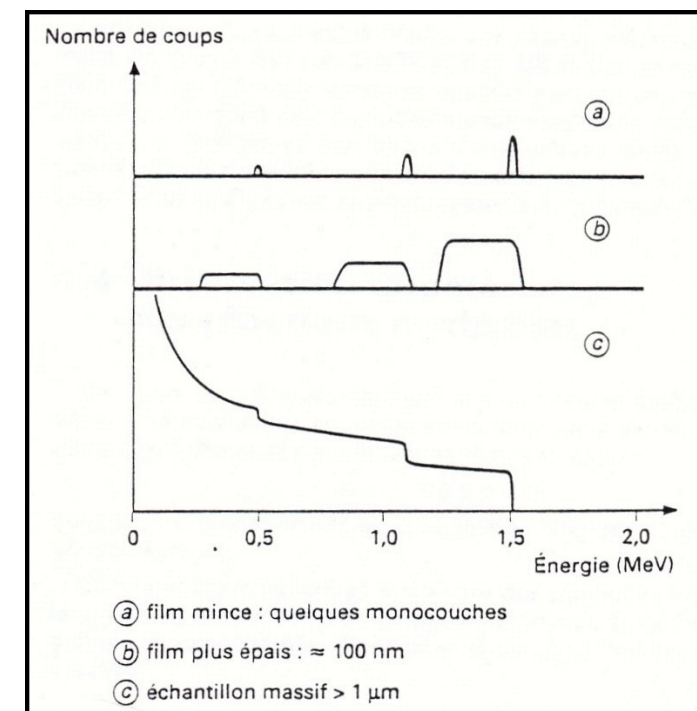
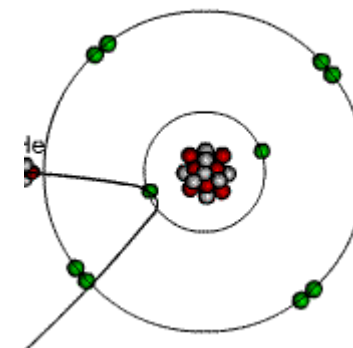
- What is the expected range of these two elements in  $\text{ZrO}_2$  ?
- What is the stopping power at the beginning of the path ( $\text{keV}/\mu\text{m}$ ) ( $d=3.97 \text{ g.cm}^{-3}$ )



## Analysis of the implanted sample with Rutherford Backscattering (RBS)

A **high energy beam** is directed at a sample. A detector is placed such that particles which scatter from the sample at close to a 180 degree angle will be collected. The energy of these ions will depend on their **incident energy** and on the **mass of the sample atom** which they hit.

RBS can be used as a means to perform a depth profile of the **composition of a sample**.



## Analysis of the implanted sample with Rutherford Backscattering (RBS)

**Exercise:** from the two following available ions which is most appropriate to analyse the implanted  $\text{Al}_2\text{O}_3$  sample i.e. to determine the implantation profile of the fission products (*the range must be sufficient for detection of backscattered ions*):

- Analysis with 2 MeV  $\text{He}^{2+}$
- Analysis with 1 and with 2 MeV  $\text{p}^+$

The following ranges have been obtained

- 70 MeV I :  $\mu\text{m}$
- 100 MeV Zr :  $\mu\text{m}$
- 2 MeV  $\text{He}^{2+}$  :  $\mu\text{m}$
- 1 MeV  $\text{p}^+$  :  $\mu\text{m}$
- 2 MeV  $\text{p}^+$  :  $\mu\text{m}$

**The 2 MeV  $\text{p}^+$  should be retained for analysis**